

WHAT IS CLAIMED IS:

1. A semiconductor light emitting diode comprising:

epitaxial growth layers including a first conductive type clad layer, an active layer made of an InGaAlP compound semiconductor on said first conductive type clad layer to generate light, and a second conductive type clad layer formed on said active layer; and

a transparent first conductive type GaP substrate made of GaP with a thickness of equal to or more than 150 μm and having a first surface, said first surface having an area equal to or wider than 0.1 mm^2 and bonded to a bonding surface of said first conductive type clad layer via no layer or via a bond layer, an area of said bonding surface of said first conductive type clad layer being smaller than said first surface of said substrate to locally expose said first surface or said bond layer.

2. A semiconductor light emitting diode according to claim 1 wherein said substrate is an approximately rectangular solid at least 350 μm wide and at least 350 μm long.

3. A semiconductor light emitting diode according to claim 1 wherein said first conductive type clad layer of said epitaxial growth layers is bonded to a central portion of said first surface of said substrate to expose an outer circumferential part of said first surface or said bond layer.

4. A semiconductor light emitting diode according to claim 3 wherein a groove is formed in said epitaxial growth layer to expose part of said first surface or said bond layer at the bottom of said groove.

5. A semiconductor light emitting diode according to claim 1 wherein the coverage of said epitaxial growth layers relative to said area of said first surface of said substrate is in the range not less than 60% and not more than 90%.

6. A semiconductor light emitting diode according to claim 1 wherein the coverage of said epitaxial growth layers relative to said area of said first surface of said substrate is in the range not less than 70% and not more than 80%.

7. A semiconductor light emitting diode according to claim 1 further comprising:

a first electrode formed on a second surface of said substrate to reflect said light from said active layer, said second surface being opposite to said first surface; and

a second electrode formed on said second conductive type clad layer,

wherein light is extracted from the side of said second conductive type clad layer.

8. A semiconductor light emitting diode comprising:

epitaxial growth layers including a first conductive type clad layer, an active layer made of an InGaAlP compound semiconductor on said first conductive type clad layer to generate light, and a second conductive type clad layer formed on said active layer;

a transparent first conductive type semiconductor substrate with a thickness of equal to or more than 150 μm being transparent to light from said active layer and having a first surface and second surface opposite to each other, said first surface having an area equal to

or wider than 0.1 mm^2 and bonded to a bonding surface of said first conductive type clad layer via no layer or via a bond layer, an area of said bonding surface of said first conductive type clad layer being smaller than said first surface of said substrate to locally expose said first surface or said bond layer, said light being extracted from the side of said second conductive type clad layer;

a first electrode formed on said second surface of said substrate to reflect said light from said active layer; and

a second electrode formed on said second conductive type clad layer.

9. A semiconductor light emitting diode according to claim 8 wherein said substrate is an approximately rectangular solid at least $350 \text{ }\mu\text{m}$ wide and at least $350 \text{ }\mu\text{m}$ long.

10. A semiconductor light emitting diode according to claim 8 wherein said first conductive type clad layer of said epitaxial growth layers is bonded to a central portion of said first surface of said substrate to expose an outer circumferential part of said first surface or said bond layer.

11. A semiconductor light emitting diode according to claim 10 wherein a groove is formed in the epitaxial growth layer to expose part of said first surface or said bond layer at the bottom of said groove.

12. A semiconductor light emitting diode according to claim 8 wherein the coverage of said epitaxial growth layers relative to said area of said first surface of said substrate is in the range not less than 60% and not more than 90%.

13. A semiconductor light emitting diode according to claim 8 wherein the coverage of said epitaxial growth layers relative to said area of said first surface of said substrate is in the range not less than 70% and not more than 80%.